L Number	Hits	Search Text	DB	Time stamp
1	115	(257/E21.623).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:39
2	705	"T-shaped gate" or "T-shaped transistor" or "T-shaped electrode"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:43
3	629	"T-shaped gate" or "T-shaped transistor" or "T-shaped electrode"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 17:49
4	154	damascene adj gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:49
5	10	("4577392" | "5808340" | "5844836" | "5960271" | "6008132" | "6044007" | "6107667" | "6136674" | "6159781" | "6333273").PN.	USPAT	2004/03/04 17:01
6	0	6551941.URPN.	USPAT	2004/03/04 17:01
7	1	("4341850").PN.	USPAT	2004/03/04 17:49
8	8	("3849136" | "3867148" | "3873361" | "3971860" | "4024293" | "4109029" | "4165395" | "4283483").PN.	USPAT	2004/03/04 17:50
9	11	4341850.URPN.	USPAT	2004/03/04 17:50
-	100	(fin near fet) or FINFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 16:27
-	84	(notch near gate) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 13:27
-	191	notch near gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 13:49
-	13	notch near transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 13:58
-	16	notch near FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 13:58
-	16	("5045488" | "5095344" | "5198380" | "5208175" | "5262655" | "5268318" | "5268319" | "5270240" | "5342801" | "5408136" | "5455792" | "5554553" | "5554564" | "5572054" | "5714412" | "5897353").PN.	USPAT	2004/03/04 13:59
-	7	6380035.URPN.	USPAT	2004/03/04 14:27
-	476	((438/259) or (438/260)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:40
-	10495	(applied near materials).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:40

-	188	((applied near materials).as.) and notch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:42
-	10008	notch and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:42
-	2350	(notch and gate) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:42
-	245	((notch and gate) and semiconductor) and amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:53
-	54	"V-shaped gate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 14:53